

WHAT IS CLAIMED IS:

1. An in-vehicle load drive-control circuit comprising:
a power MOSFET ^B ~~between~~ connected in series between a load ^{LM1}
and a power source, ^D the power MOSFET on/off controlling the
power supply to the load, the power MOSFET incorporating a
thermoelectric element ^D across which the voltage drops owing
to heat liberation when the power MOSFET is energized; and
a control means ^{CPT} for ON/OFF controlling a gate driving
signal to the power MOSFET on the basis of ² (a) voltage drop,
wherein after the voltage has been stabilized, the gate
driving signal is made constant.
2. An in-vehicle load drive-controlling circuit according
to claim 1, wherein the control means comprises a rush current
detecting unit ^{DTI1} for detecting a rush current to the load on the
basis of a time changing rate of ^{N.A.B.} the voltage drop to produce
an interrupting signal for the gate driving signal to the power
MOSFET.
3. An in-vehicle load drive-controlling circuit according
to claim 2, wherein the control means comprises an abnormal
current detecting unit ^{DTI2} for deciding an excess current due to
poor wiring when the number of times of detecting the rush current
by the rush current detecting unit is more than a prescribed
number to produce an interrupting signal for the gate driving
signal to the power MOSFET.
4. An in-vehicle load drive-controlling circuit according
to claim 2, wherein the rush current detecting unit produces

the gate driving signal at intervals while a load current is suppressed to less than a prescribed current after the voltage across the thermoelectric element has dropped to a prescribed voltage to repeat an ON/OFF operation of the power MOSFET so that the voltage is increased by a certain degree by heat dissipation of the power MOSFET.

5. An in-vehicle load drive-controlling circuit according to claim 2, wherein the rush current detecting unit produces the gate driving signal at intervals while a load current is suppressed to less than a prescribed current after the voltage across the thermoelectric element has dropped to a prescribed voltage to repeat an ON/OFF operation of the power MOSFET and ON/OFF operation of energization of a load is repeated so that heat liberation of the load is stabilized to make resistance constant.

6. An in-vehicle load drive-controlling circuit according to claim 1, wherein the control unit comprises an overheat detecting unit for detecting overheat abnormality of the power MOSFET when the voltage drops to produce an interrupting signal for the gate driving signal.

7. An in-vehicle load drive-controlling circuit according to claim 6, wherein the overheat detecting unit decides restoration of the overheat abnormality of the power MOSFET when the voltage rises, thereby producing the gate driving signal.

8. An in-vehicle load drive-controlling circuit according to claim 1, wherein the thermoelectric element is a diode whose forward voltage increases with an increase in an ambient temperature.

9. An in-vehicle load drive-controlling circuit according to claim 1, wherein it further comprises a plurality of power MOSFETs for driving a plurality of loads, respectively, and the control unit supplies gate driving signals at slight intervals over time to the gates of these MOSFETs.

10. An in-vehicle load drive-controlling circuit according to claim 1, wherein the control unit supplies the gate driving signal based on a PWM signal to the power MOSFET.